

P-Channel Power MOSFET

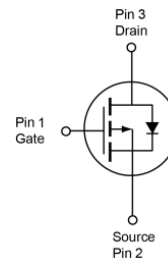
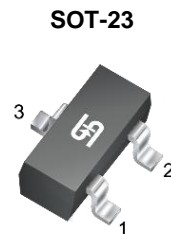
FEATURES

- Advance trench process technology
- RoHS compliant
- Halogen-free

APPLICATIONS

- Power management
- Load switch
- Battery protection

KEY PERFORMANCE PARAMETERS		
PARAMETER	VALUE	UNIT
V_{DS}	-20	V
$R_{DS(on)}$ (max)	$V_{GS} = -4.5V$	55
	$V_{GS} = -2.5V$	80
	$V_{GS} = -1.8V$	130
Q_g	9.5	nC



Note: MSL 1 (Moisture Sensitivity Level) per J-STD-020

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ C$ unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 8	V
Continuous Drain Current	I_D	-3.6	A
Pulsed Drain Current (Note 1)	I_{DM}	-14.4	A
Total Power Dissipation	P_D	$T_A = 25^\circ C$	1.04
		$T_A = 70^\circ C$	0.67
Operating Junction and Storage Temperature Range	T_J, T_{STG}	- 55 to +150	$^\circ C$

THERMAL PERFORMANCE			
PARAMETER	SYMBOL	LIMIT	UNIT
Junction to Ambient Thermal Resistance (Note 2)	$R_{\theta JA}$	120	$^\circ C/W$

Notes:

1. Pulse Width $\leq 100\mu s$.
2. Device on a PCB FR4 with 1 in² (single layer, 2 oz thickness) copper area for drain connection.

ELECTRICAL SPECIFICATIONS ($T_A = 25^\circ\text{C}$ unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static (Note 3)						
Drain-Source Breakdown Voltage	$V_{GS} = 0\text{V}, I_D = -250\mu\text{A}$	BV_{DSS}	-20	--	--	V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\mu\text{A}$	$V_{GS(TH)}$	-0.45	-0.6	-1	V
Gate Body Leakage	$V_{GS} = \pm 8\text{V}, V_{DS} = 0\text{V}$	I_{GSS}	--	--	± 100	nA
Zero Gate Voltage Drain Current	$V_{DS} = -20\text{V}, V_{GS} = 0\text{V}$	I_{DSS}	--	--	-1	μA
Drain-Source On-State Resistance	$V_{GS} = -4.5\text{V}, I_D = -3.6\text{A}$	$R_{DS(on)}$	--	28	55	m Ω
	$V_{GS} = -2.5\text{V}, I_D = -3\text{A}$		--	35	80	
	$V_{GS} = -1.8\text{V}, I_D = -2.1\text{A}$		--	46	130	
Forward Transconductance	$V_{DS} = -10\text{V}, I_D = -0.9\text{A}$	g_{fs}	--	8.7	--	S
Dynamic (Note 4)						
Total Gate Charge	$V_{DS} = -10\text{V}, I_D = -3.6\text{A}, V_{GS} = -4.5\text{V}$	Q_g	--	9.5	--	nC
Gate-Source Charge		Q_{gs}	--	0.9	--	
Gate-Drain Charge		Q_{gd}	--	2.4	--	
Input Capacitance	$V_{DS} = -10\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$	C_{iss}	--	771	--	pF
Output Capacitance		C_{oss}	--	114	--	
Reverse Transfer Capacitance		C_{rss}	--	100	--	
Gate Resistance	$f = 1.0\text{MHz}$	R_g	--	13	--	Ω
Switching (Note 5)						
Turn-On Delay Time	$V_{DD} = -10\text{V}, R_G = 6\Omega, I_D = -3.6\text{A}, V_{GS} = -4.5\text{V}$	$t_{d(on)}$	--	4.6	--	ns
Turn-On Rise Time		t_r	--	2.4	--	
Turn-Off Delay Time		$t_{d(off)}$	--	96	--	
Turn-Off Fall Time		t_f	--	42	--	
Source-Drain Diode						
Forward Voltage (Note 3)	$I_S = -3.6\text{A}, V_{GS} = 0\text{V}$	V_{SD}	--	0.7	1.2	V

Notes:

- Pulse test: Pulse Width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.
- Defined by design. Not subject to production test.
- Switching time is essentially independent of operating temperature.

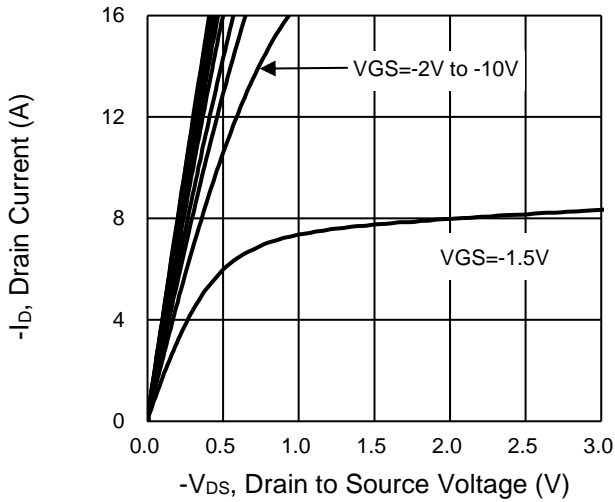
ORDERING INFORMATION

ORDERING CODE	PACKAGE	PACKING
TSM2305CX RFG	SOT-23	3kpcs / 7" Reel

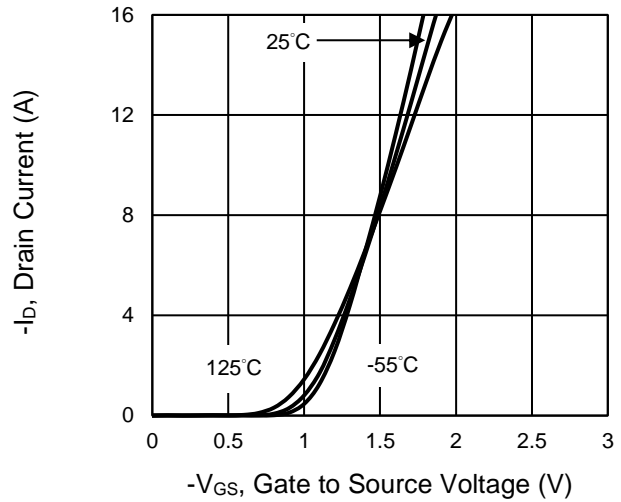
CHARACTERISTICS CURVES

($T_A = 25^\circ\text{C}$ unless otherwise noted)

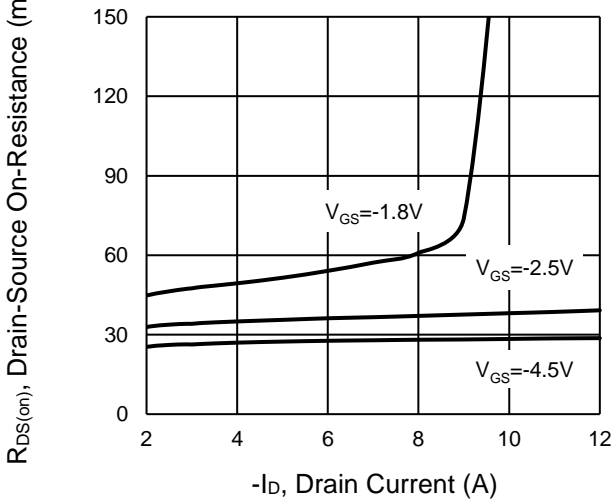
Output Characteristics



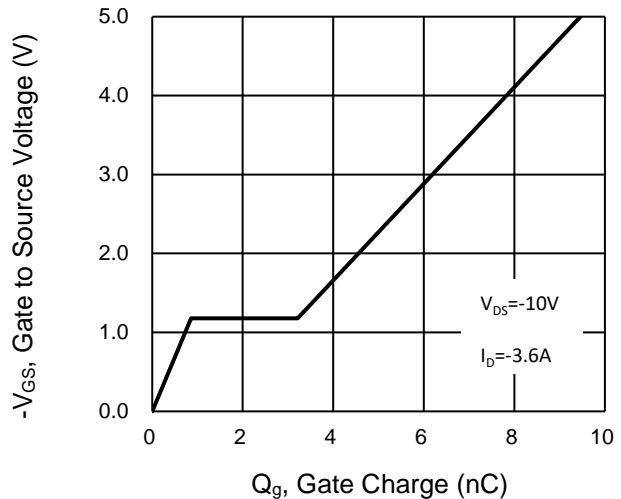
Transfer Characteristics



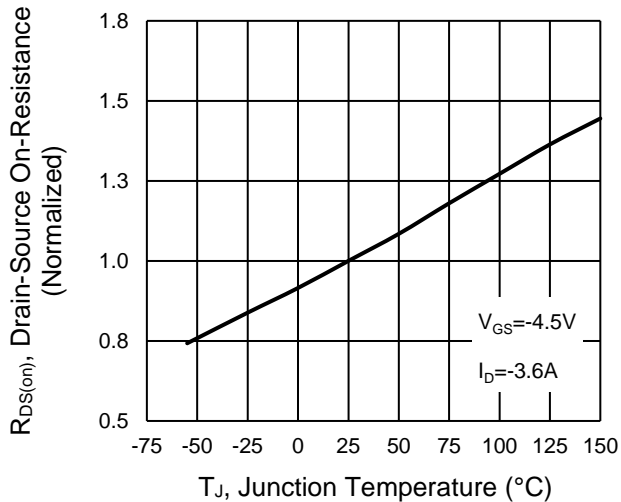
On-Resistance vs. Drain Current



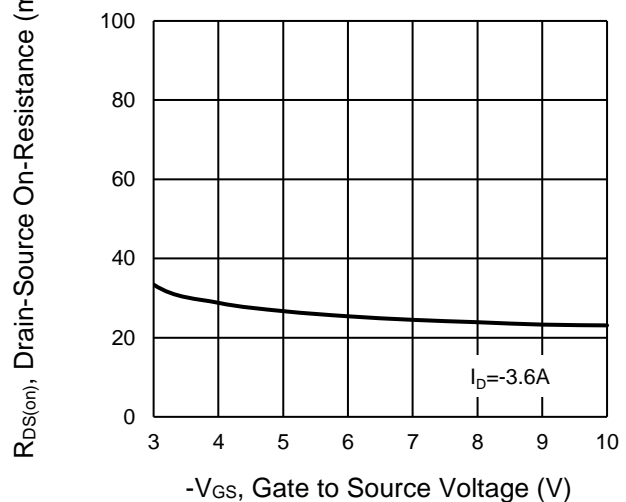
Gate-Source Voltage vs. Gate Charge



On-Resistance vs. Junction Temperature



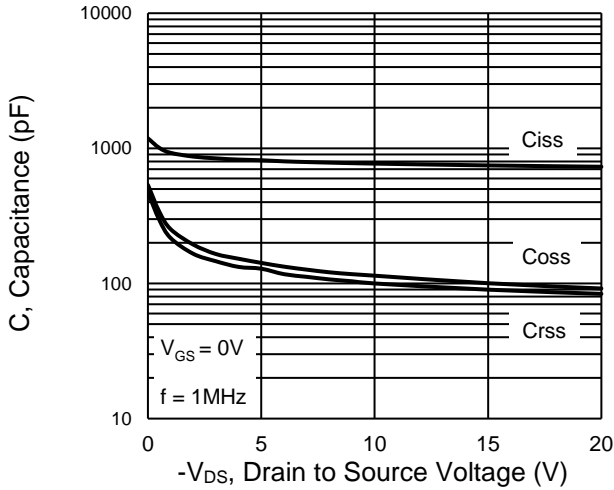
On-Resistance vs. Gate-Source Voltage



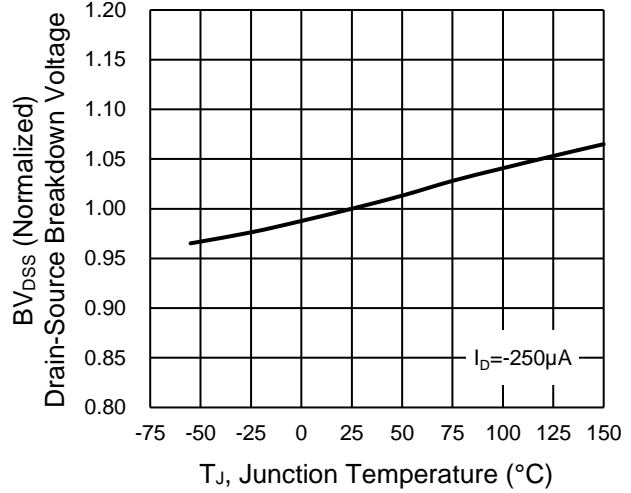
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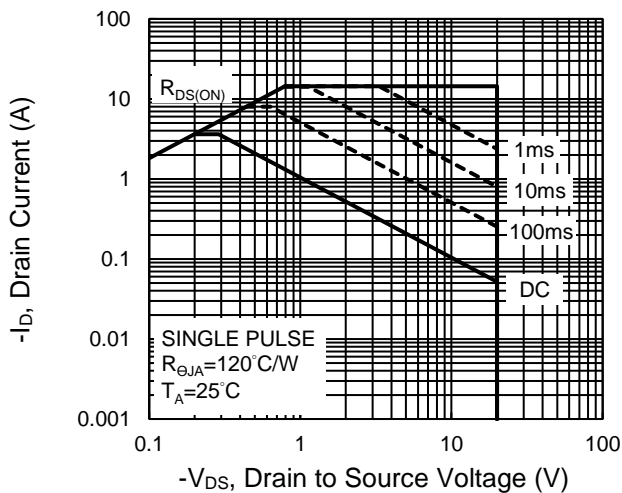
Capacitance vs. Drain-Source Voltage



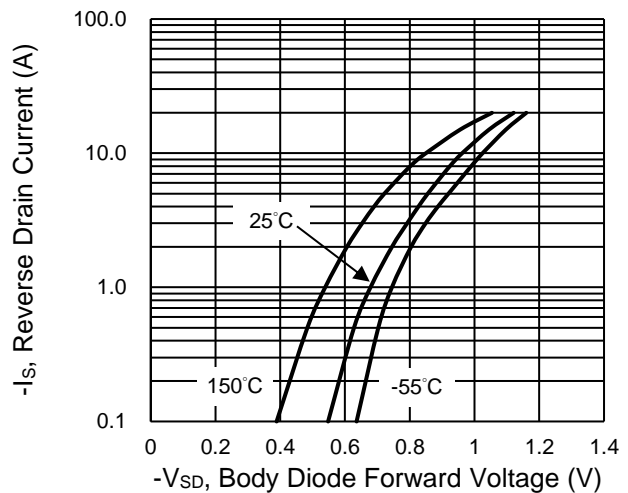
BV_{DSS} vs. Junction Temperature



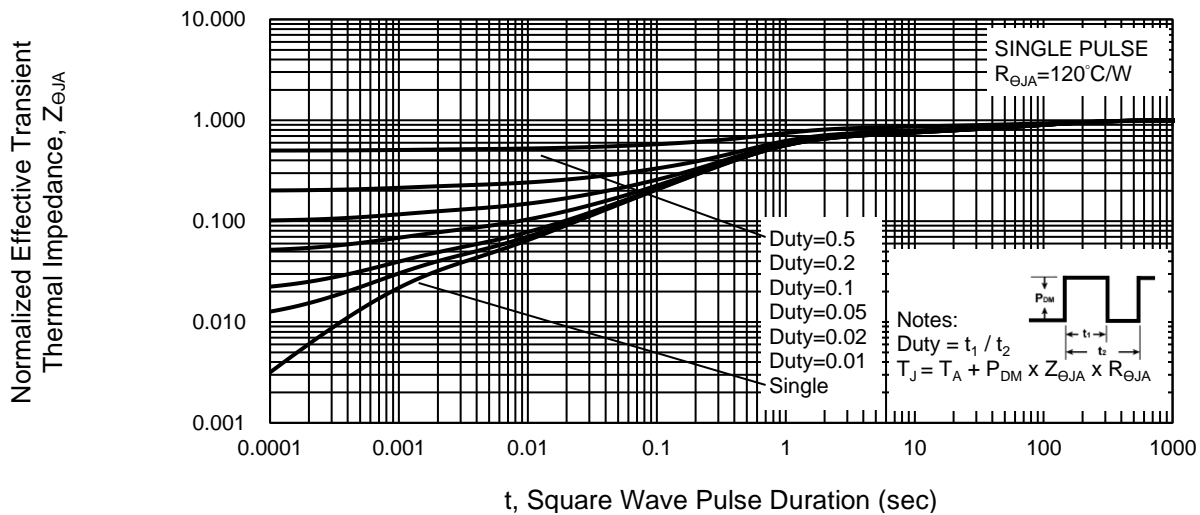
Maximum Safe Operating Area, Junction-to-Ambient



Source-Drain Diode Forward Current vs. Voltage



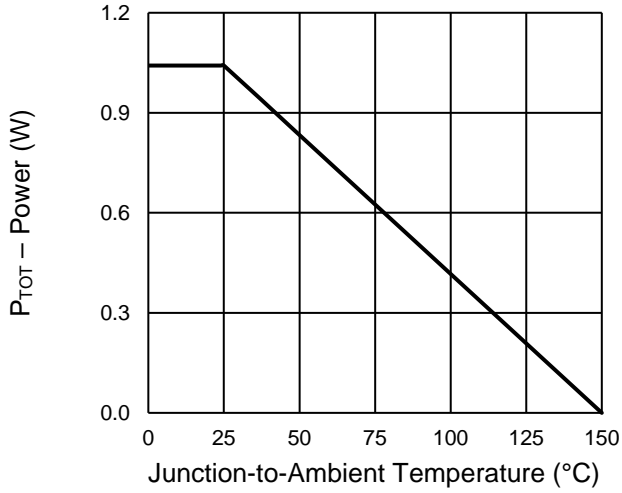
Normalized Thermal Transient Impedance, Junction-to-Ambient



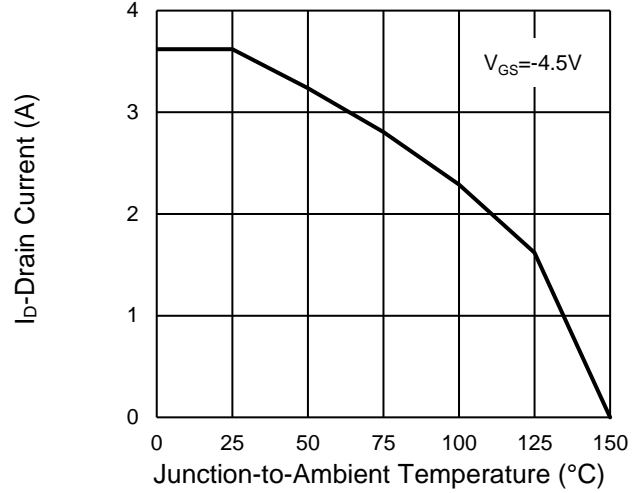
CHARACTERISTICS CURVES

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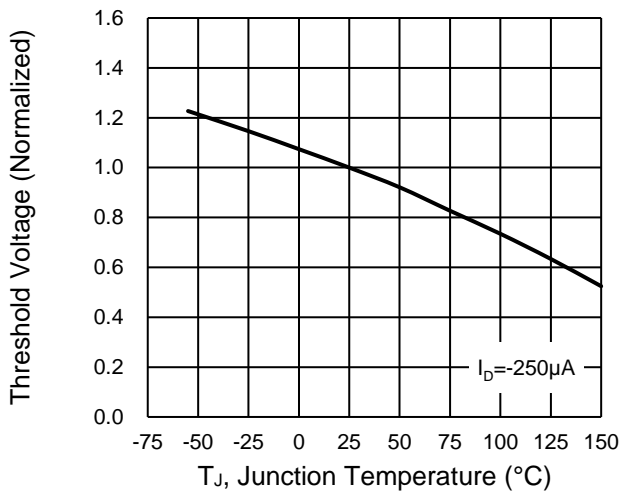
Power Dissipation



Drain Current

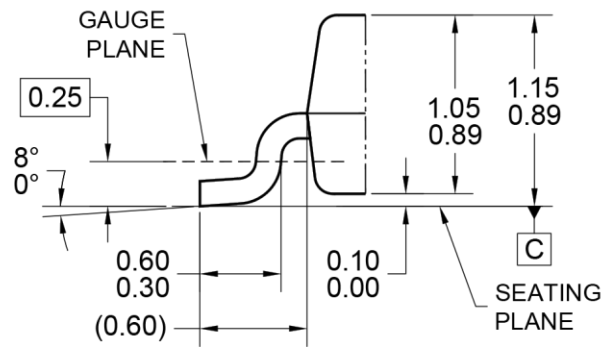
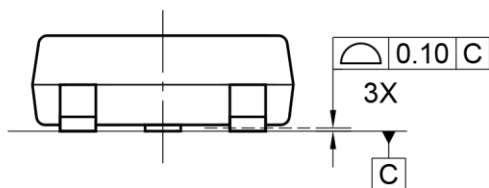
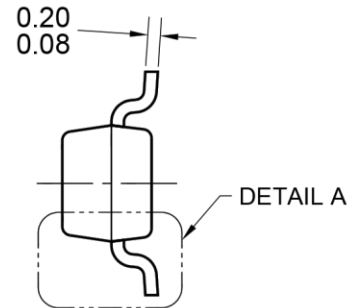
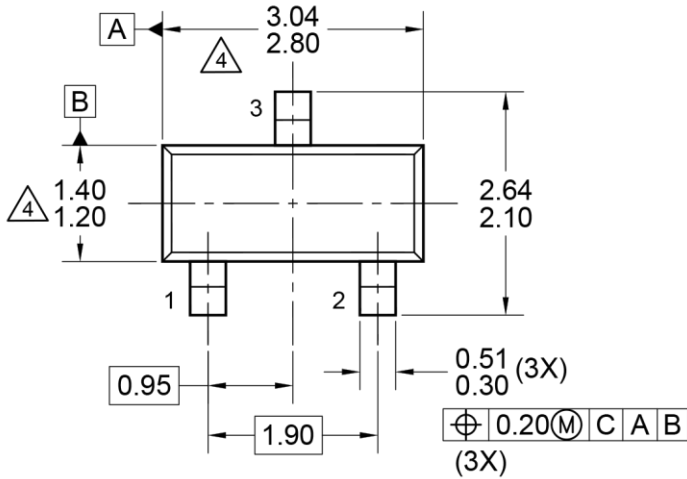


Normalized gate threshold voltage vs Temperature

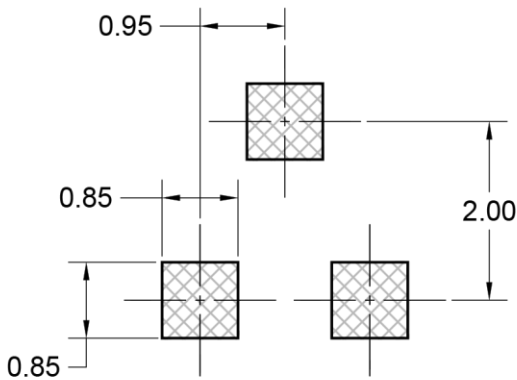


PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

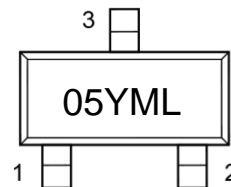
SOT-23



DETAIL A, ROTATED -90°
(SCALE 2:1)



SUGGESTED PAD LAYOUT



MARKING DIAGRAM

NOTES: UNLESS OTHERWISE SPECIFIED

1. ALL DIMENSIONS ARE IN MILLIMETERS.
2. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
3. PACKAGE OUTLINE REFERENCE: JEDEC TO-236, ISSUE H, VARIATION AA.
4. MOLDED PLASTIC BODY DIMENSIONS DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
5. DWG NO. REF: HQ2SD07-SOT23JEDEC-104 REV A.

- 05 = Device marking
- Y = Year Code
- M = Month Code for Halogen Free Product
(O=Jan, P=Feb, Q=Mar, R=Apl, S=May, T=Jun, U=Jul, V=Aug, W=Sep, X=Oct, Y=Nov, Z=Dec)
- L = Lot Code

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